

Abstract of the Disclosure:

The invention relates to an electronic device and a semiconductor wafer and also to a method for producing the device and wafer. The electronic device comprises at least one 5 semiconductor chip obtained from corresponding chip positions of a semiconductor wafer constructed according the invention. In this case, the semiconductor chip has two topmost metallization layers that have area-covering voltage supply structures, insulation layers arranged in between, and passage 10 contacts to module regions of an integrated circuit. The voltage supply structure has a grid of supply interconnects arranged parallel to one another. This grid is rotated with respect to a grid of a subsequent metallization layer.

15

MPW/nt